CHENMKO ENTERPRISE CO.,LTD

Lead free devices

SURFACE MOUNT
NPN SILICON Transistor
VOLTAGE 200 Volts CURRENT 0.6 Ampere

CHT2000ZPT

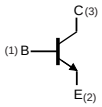
APPLICATION
* Telephony and proferssional communction equipment.
* Other switching applications.

FEATURE
* Small flat package. (SC-73/SOT-223)
* Suitable for high packing density.
* High saturation current capability.

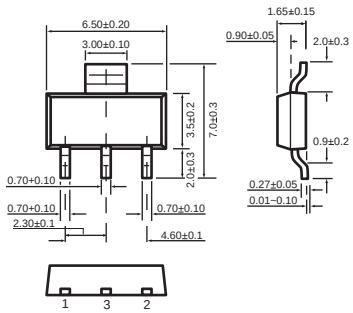
CONSTRUCTION
* NPN SILICON Transistor

MARKING
ZMN

CIRCUIT



SC-73/SOT-223



1 Base
2 Emitter
3 Collector (Heat Sink)

Dimensions in millimeters

SC-73/SOT-223

LIMITING VALUES
In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	200	V
V_{CEO}	collector-emitter voltage	open base	–	200	V
V_{EBO}	emitter-base voltage	open collector	–	10	V
I_C	collector current (DC)		–	600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	2	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CHT2000ZPT)

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise speciÞed.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	V_{CB} = 180 V	–	500	nA
I_{EBO}	emitter cut-off current	V_{EB}=10V	–	100	nA
h_{FE}	DC current gain	I_C = 100uA; V_{CE} = 5V I_C = 10mA; V_{CE} = 5V I_C = 160mA; V_{CE} =5V	3000 3000 3000	– – –	
V_{CEsat}	collector-emitter saturation voltage	I_C = 20 mA; I_B =25uA	–	0.9	V
		I_C =80 mA; I_B = 40uA	–	1.1	V
		I_C =160mA; I_B =100uA	–	1.2	V
V_{BEON}	base-emitter saturation voltage	V_{CE}=5V,I_C=160mA	–	2.0	V